



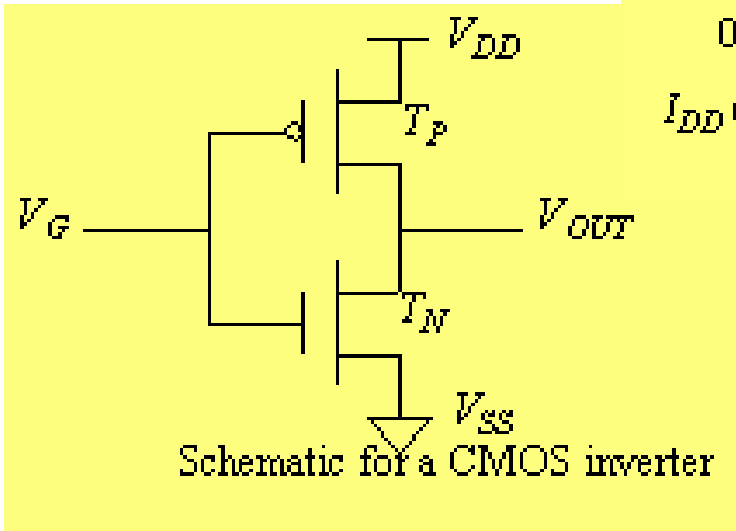
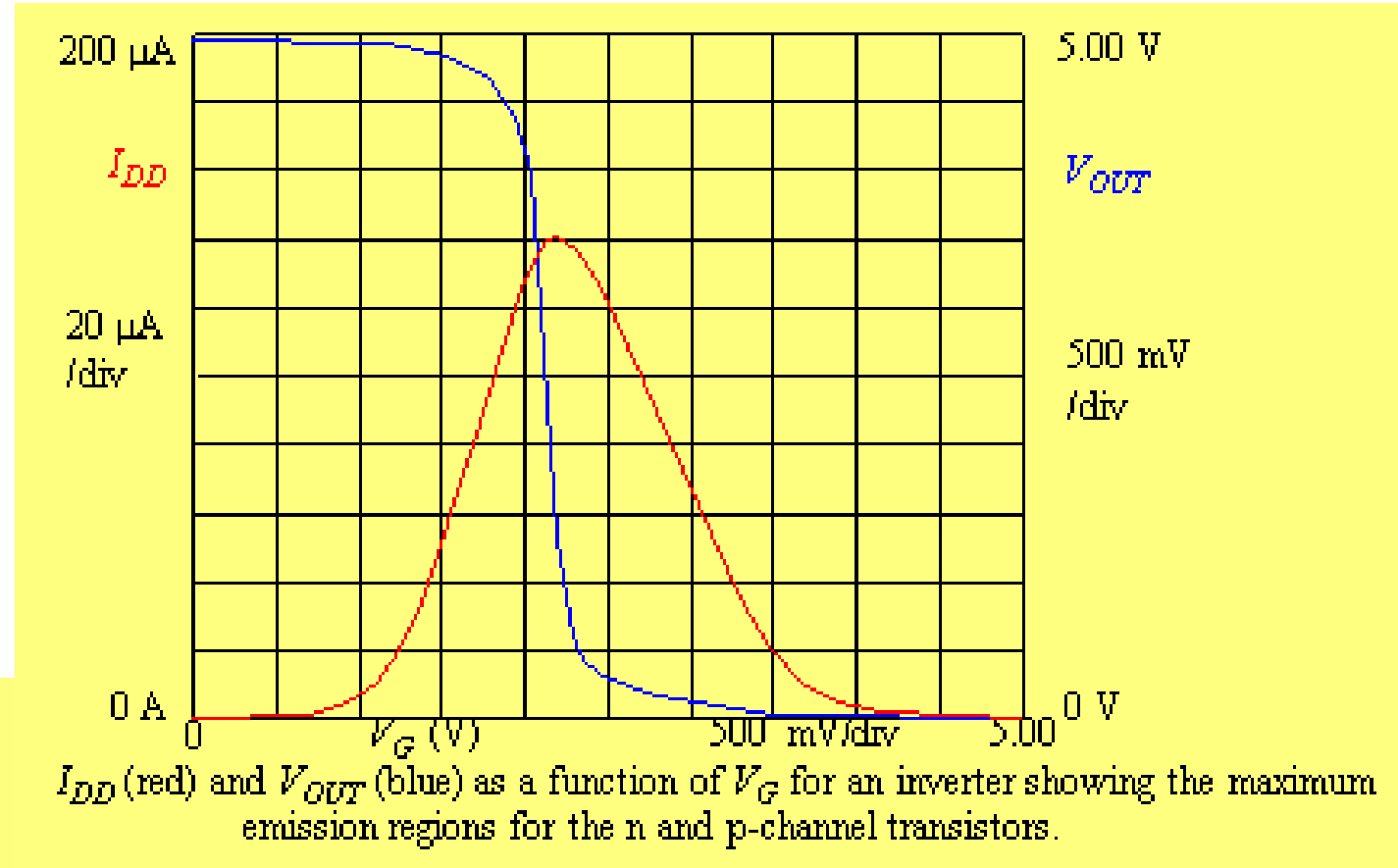
Dynamic Emission microscopy background

Philippe Perdu CNES Toulouse



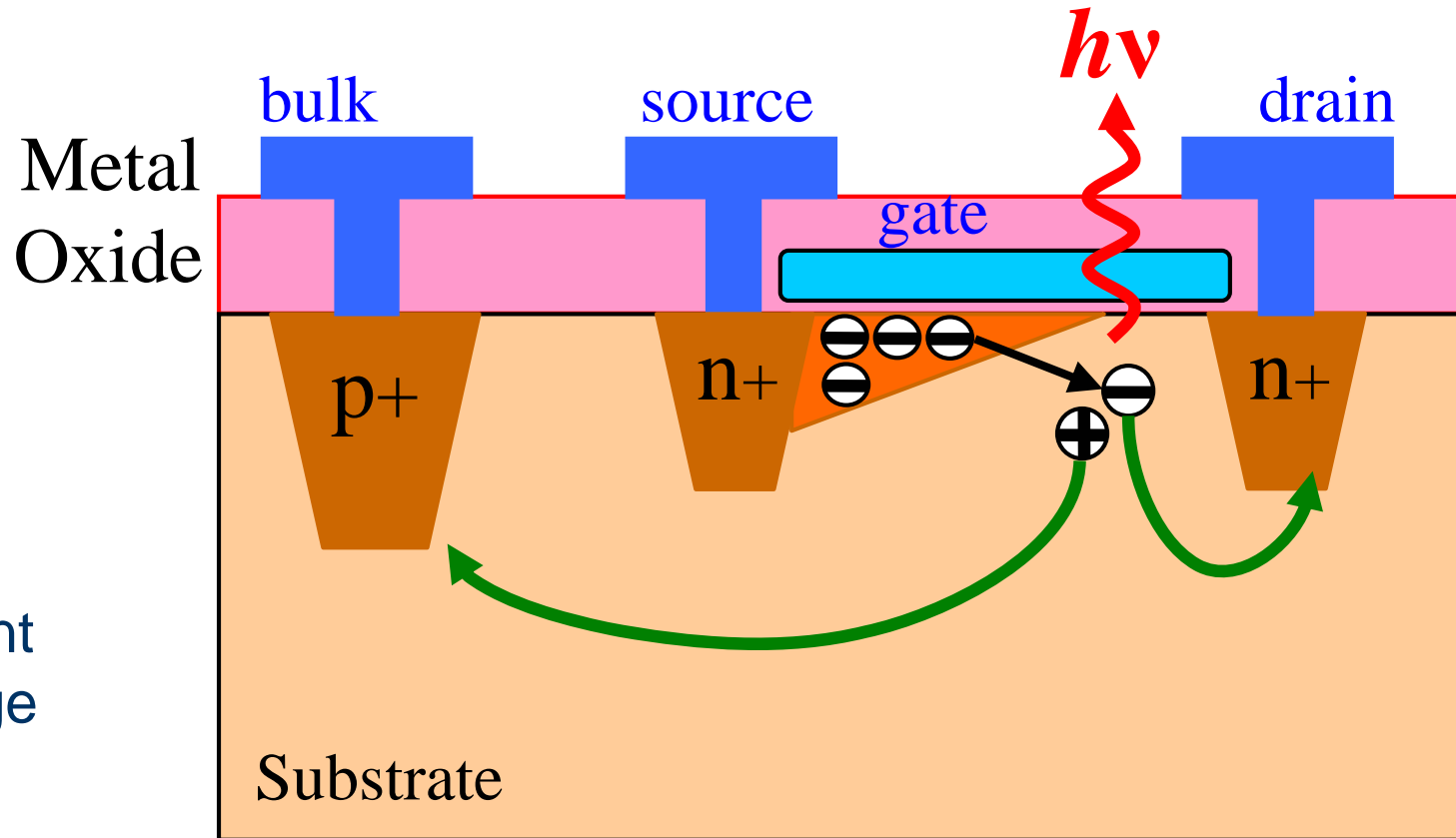
- *Dynamic emission principle*
- *Single points detectors*
- *Image detectors*
- *Applications*
- *Challenges*

Dynamic emission principle (1)



P max around $V_{DS}/2$

Dynamic emission principle (2)

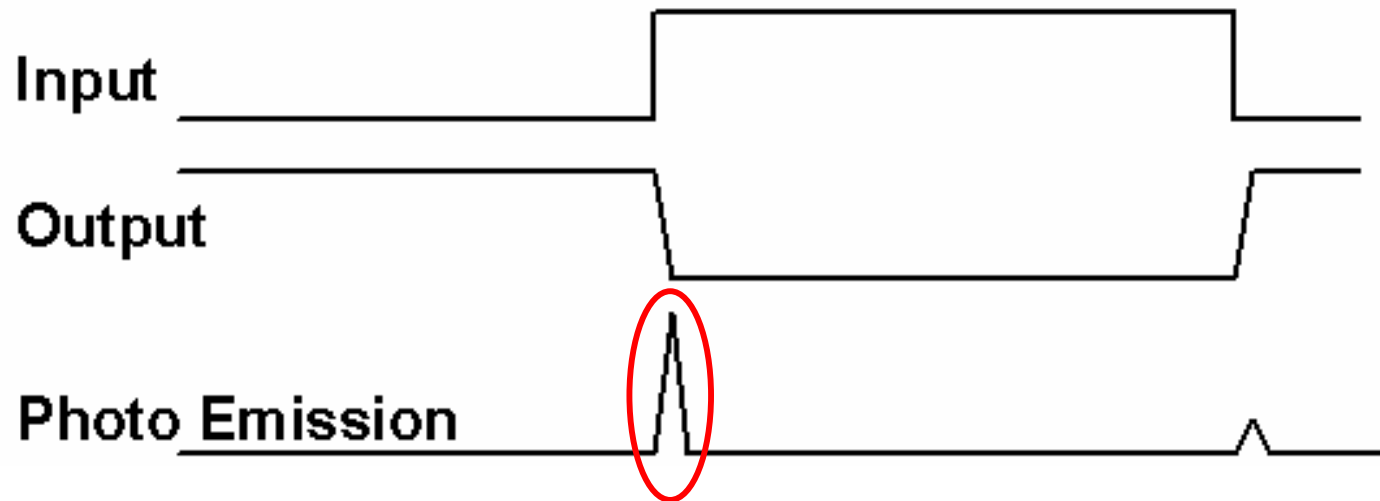
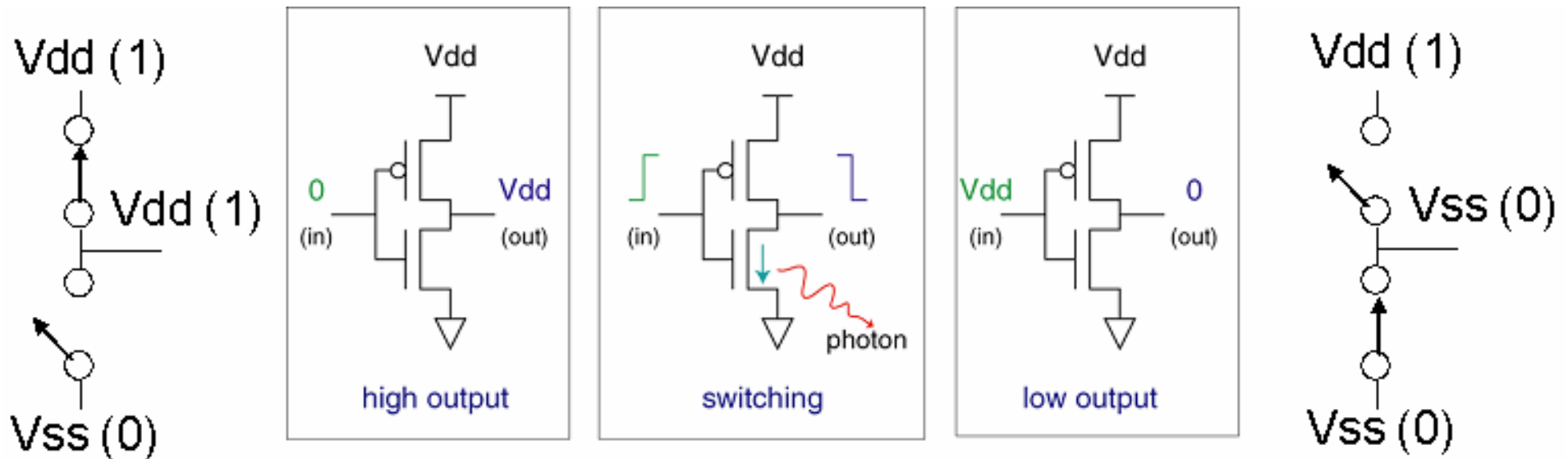


Need

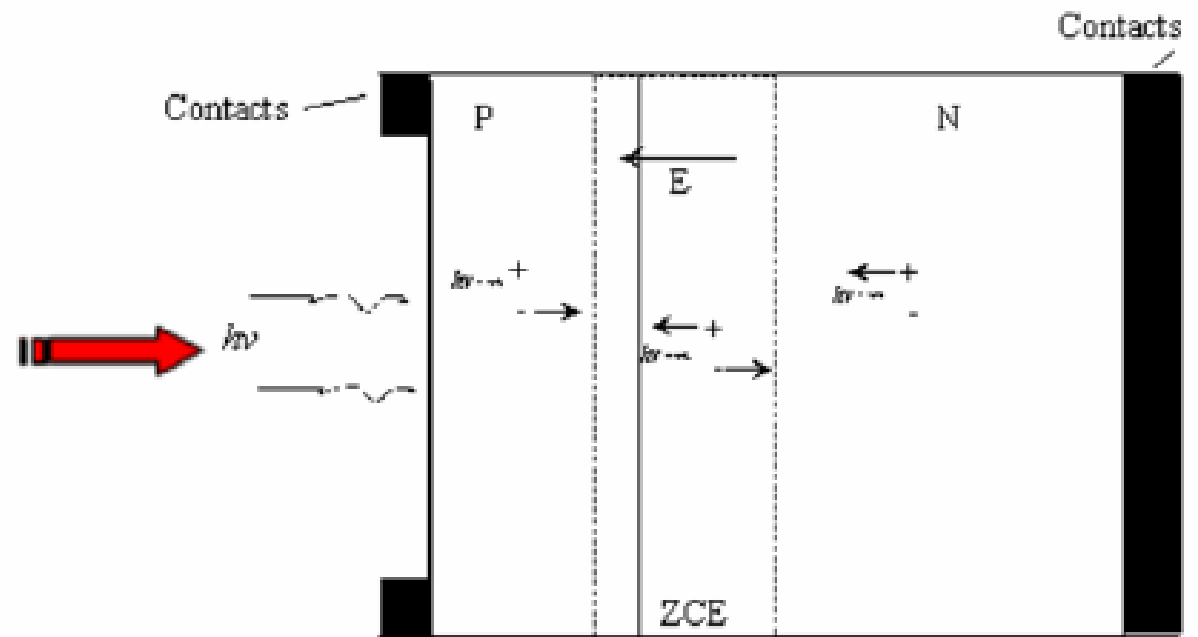
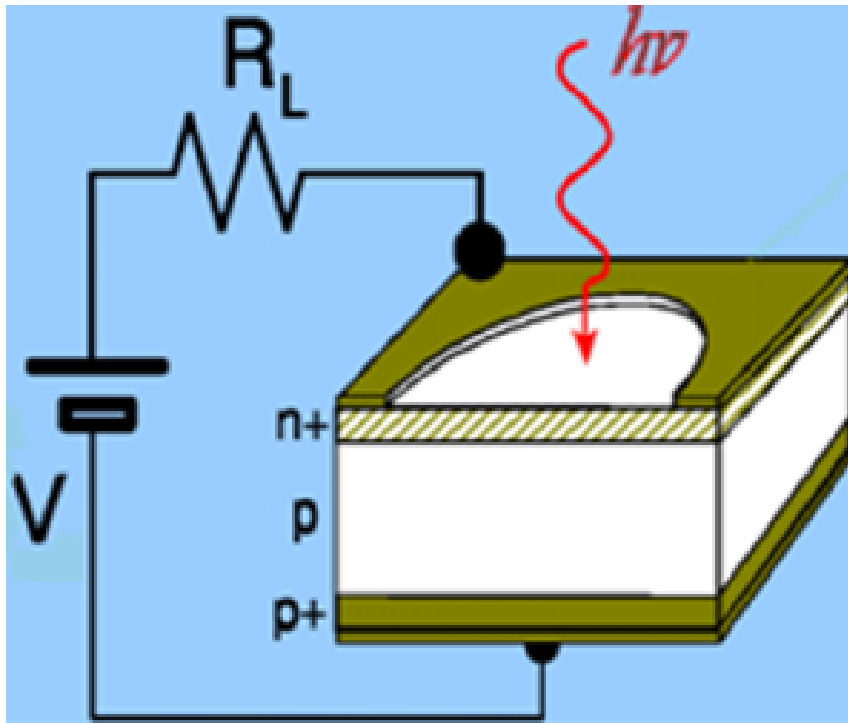
- Current
- Voltage

$$N_{ph} = A \frac{I_s}{q} (V_{DS} - V_{DSsat}) \exp\left(-\frac{B}{V_{DS} - V_{DSsat}}\right)$$

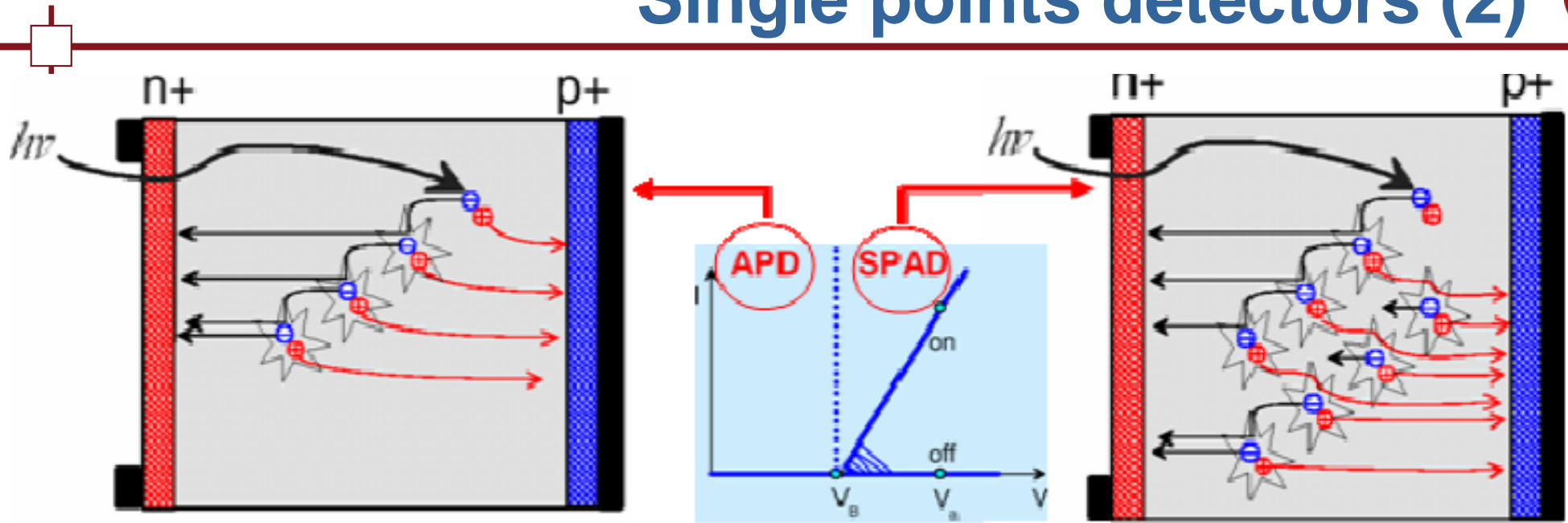
Dynamic emission principle (3)



- *Photodiodes: photon / current conversion*



Single points detectors (2)



➤ 2 principles

■ Geiger mode (SPAD)

- ultra sensitive: QE = 100%
- Very instable, lot of noise

■ Avalanche mode

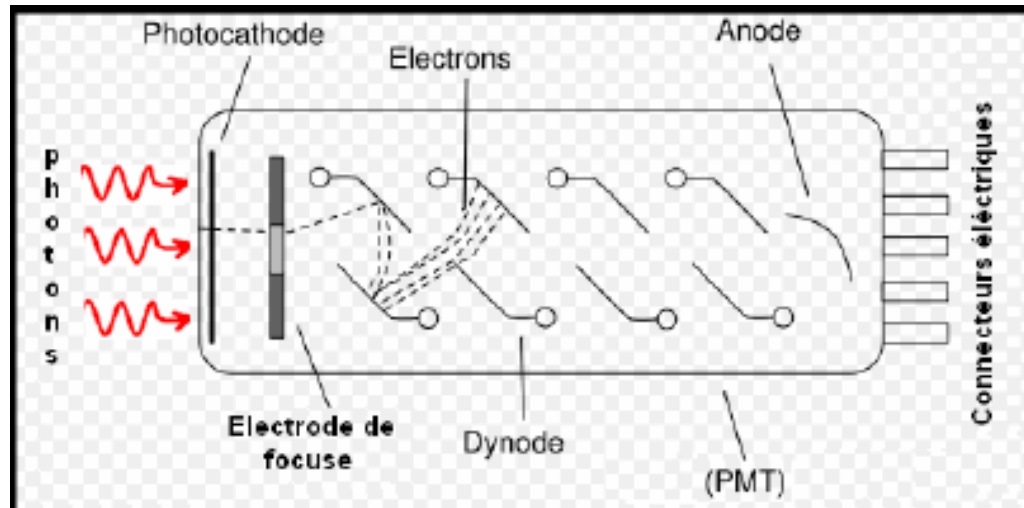
- Reverse biased, close to V_B
- Quite instable, more noise than linear mode

➤ Need quenching (passive or active)

Best choice InGaAs APD

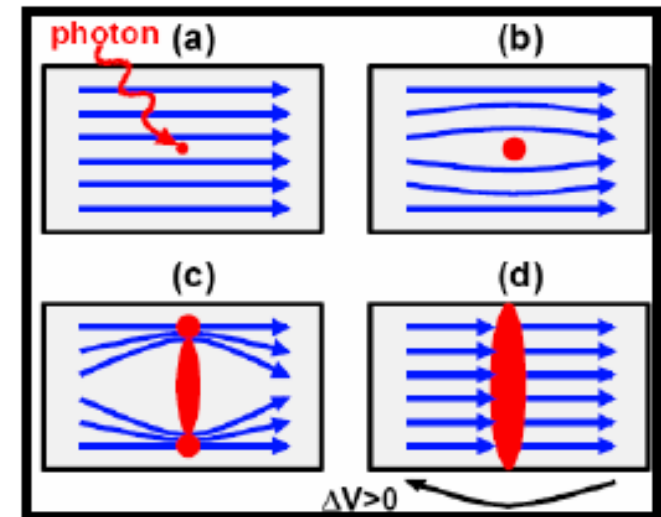
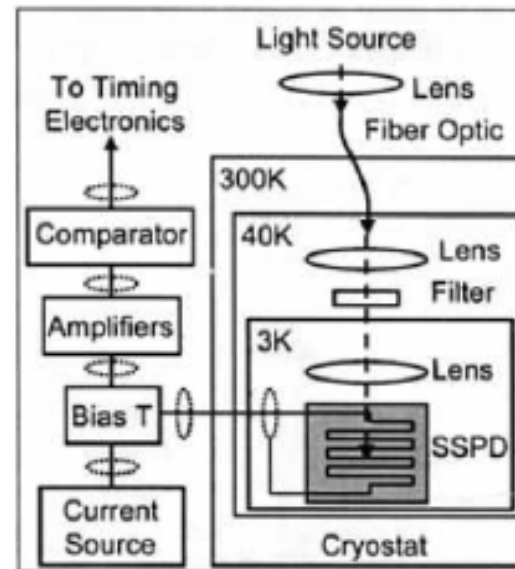
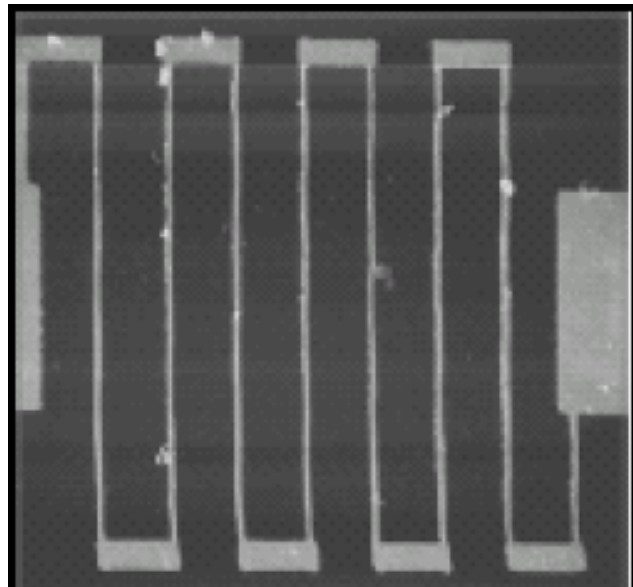
- Backside
- Bandwidth up to 1.7 μm

Single points detectors (3)



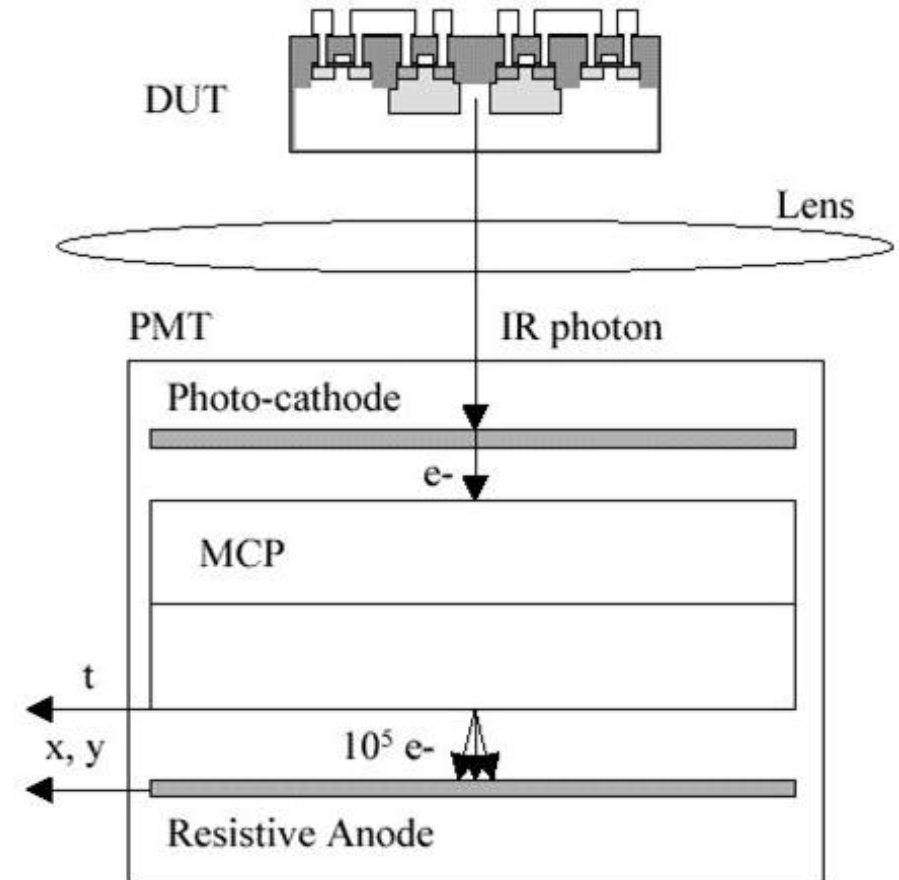
PMT

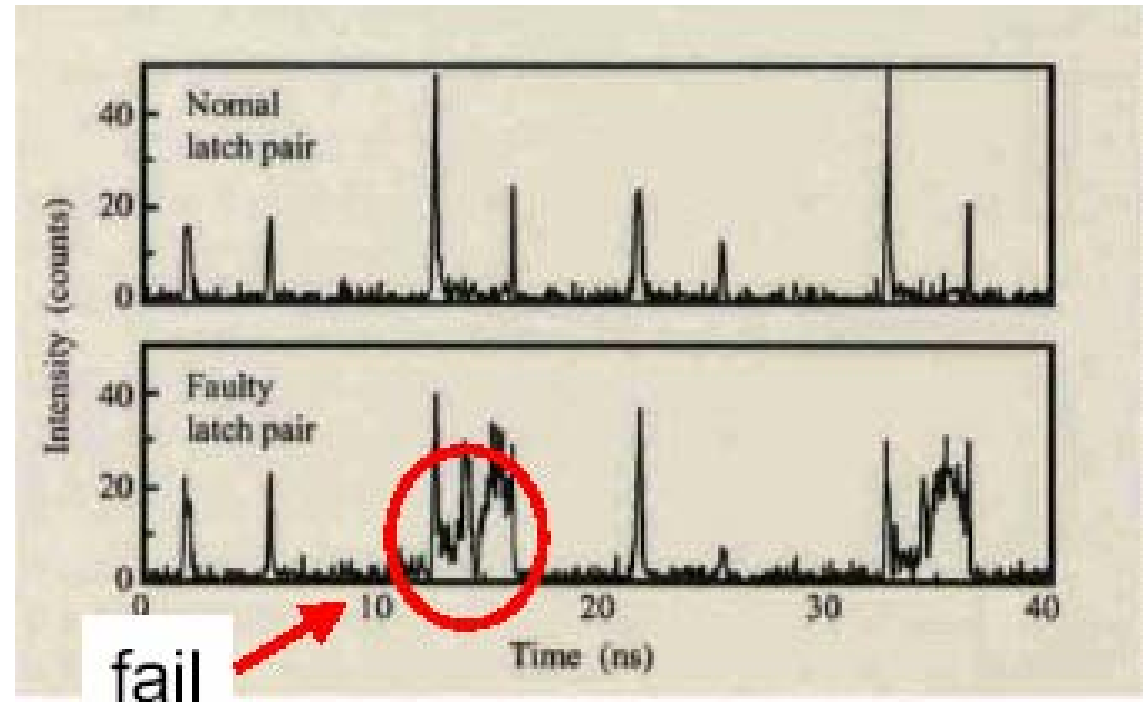
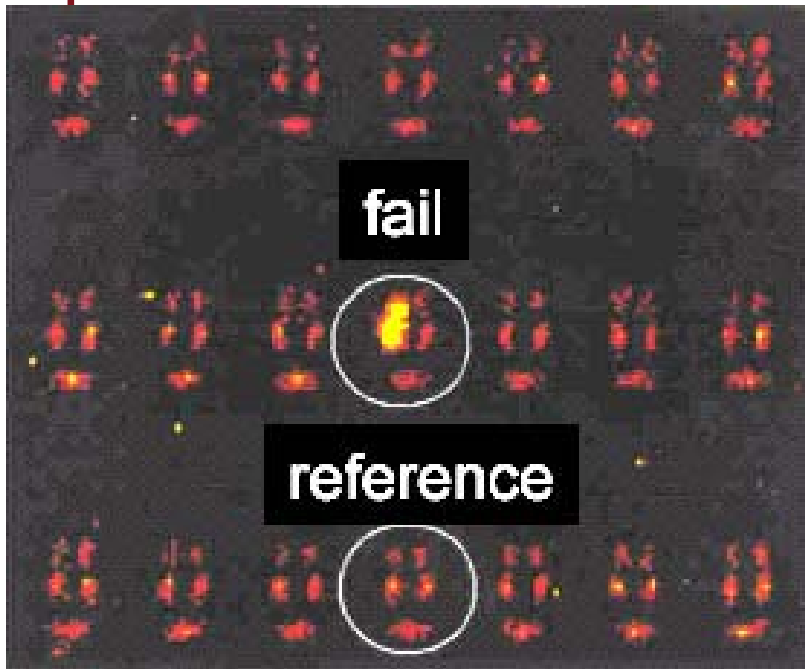
- Low QE and noise
- no Quenching



SSPD (NbN) faster

- *Single point (Time Resolved Emission)*
- *Image mode (based on PMT) except:*
 - MCP (Multi Channel Plate) to keep the position
 - Resistive Anode (to detect the position)
- *PICA (Picosecond Imaging Circuit Analysis)*
 - Mepsicron 2 (S25)
 - Limited to 900 nm
- *Time Resolved Tmaging*
 - InGaAs Photocathode





- *Light emission coming from a shift register activated by a test pattern that demonstrates the defect*
- *From Freescale*

- *Optical waveforms of the reference gate from the golden device and of the faulty one*
- *Other applications (image modes)*



- *Emission of photons decreases strongly with the lowering of VDD power supply*
- *Long acquisition time needed to get the right SNR*
- *Where to probe?*
 - Lack of hypothesis or CAD
 - No emission (why? Bad node probed or detection issue)
 - Time Resolved Imaging can help a lot